

ABSTRACT OF THE DISCLOSURE

A semiconductor device containing a multi-layered wiring structure formed on a semiconductor substrate, the structure including at least two wiring layers formed in an interlayer insulation layer, and each of the wiring layers including a metal wiring made of one of Cu and a Cu alloy, wherein the multi-layered wiring structure comprises a lower wiring layer formed under the interlayer insulation layer, a via buried in the interlayer insulation layer to connect an upper wiring layer and the lower wiring layer, and a dummy via buried in the interlayer insulation layer, the dummy via being not connected to the upper wiring layer.